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Eğitim Bilgileri

Doktora, Georgia State University, Physics & Astronomy, Amerika Birleşik Devletleri 2004 - 2008
Yüksek Lisans, Georgia State University, Physics&Astronomy, Amerika Birleşik Devletleri 2001 - 2004
Yüksek Lisans, Marmara Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Yl) (Tezli), Türkiye 1998 - 2001
Lisans, Marmara Üniversitesi, Fen - Edebiyat Fakültesi, Fizik Bölümü, Türkiye 1994 - 1998

Yaptığı Tezler

Doktora, Growth and characterization of indium nitride layers grown by high-pressure chemical vapor deposition, Georgia State University, Physics & Astronomy, 2005
Yüksek Lisans, Cut off wavelength dependence on doping concentration for highly doped p-type GaAs detector structures, Georgia State University, Physics&Astronomy, 2001
Yüksek Lisans, Titanyum atomunun toplam ve kısmi fotoiyonlaşma tesir kesiti hesapları, Marmara Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Yl) (Tezli), 2001

Araştırma Alanları

Baskı Devreler, İnce Film, Kalın Film ve Hibrid Tümleşik Devreler, Dönüştürücüler ve Algılama Aygıtları , Nanoteknoloji, Optik ve Fotonik, Aydınlatma Teknolojisi , Yenilenebilir Enerji, Dielektrik Malzeme ve Aygıtlar , Optik Malzeme ve Aygıtlar , Optoelektronik Malzeme ve Aygıtlar , Yarı İletken Malzeme ve Aygıtlar , Güneş Enerjisi, Fizik, Atomik Özellikler ve Fotonla Etkileşmeler, Moleküler Özellikler ve Fotonla Etkileşmeler, Disiplinlerarası Fizik ve İlgili Bilim ve Teknoloji Alanları, Optik, Yoğun Madde 1:Yapısal, Mekanik ve Termal Özellikler

Akademik Unvanlar / Görevler

Prof.Dr., Marmara Üniversitesi, Fen - Edebiyat Fakültesi, Fizik Bölümü, 2019 - Devam Ediyor
Doç.Dr., Marmara Üniversitesi, Fen - Edebiyat Fakültesi, 2013 - 2019
Yrd.Doç.Dr., Marmara Üniversitesi, Fen - Edebiyat Fakültesi, Fizik Bölümü, 2011 - 2013
Uzman, İhsan Doğramacı Bilkent Üniversitesi, Ulusal Nanoteknoloji Uygulama Ve Araştırma Merkezi, 2010 - 2011
Öğretim Görevlisi Dr., University of Nevada, Las Vegas, Harry Reid Center For Enviromental Studies, 2010 - 2010
Öğretim Görevlisi, Georgia State University, College Of Arts And Sciences, Physics And Astronomy, 2008 - 2010

Araştırma Görevlisi, Georgia State University, College Of Arts & Sciences, Physics & Astronomy, 2001 - 2008
Araştırma Görevlisi, Marmara Üniversitesi, Fen - Edebiyat Fakültesi, Fizik Bölümü, 1998 - 2001

Akademik İdari Deneyim

Marmara Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Yl) (Tezli) (İngilizce), 2011 - Devam Ediyor

Yönetilen Tezler

Alevli M., Optical Properties of Group III Nitride Thin films grown by hollow cathode plasma assisted atomic layer deposition, Doktora, N.Güngör(Öğrenci), 2019
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SCI, SSCI ve AHCI İndekslerine Giren Dergilerde Yayınlanan Makaleler

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VI. **Influence of N-2/H-2 and N-2 plasma on binary III-nitride films prepared by hollow-cathode plasma-assisted atomic layer deposition**
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VII. **Enhancement in c-Si solar cells using 16 nm InN nanoparticles**
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VIII. **Comparison of trimethylgallium and triethylgallium as "Ga" source materials for the growth of ultrathin GaN films on Si (100) substrates via hollow-cathode plasma-assisted atomic layer deposition**
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XIII. **Thermal stability of InN epilayers grown by high pressure chemical vapor deposition**
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XXXV. **Equation of state of alkane and alkylbenzene liquids: A test of the group contributions of scaling parameters for physical and chemical mixtures**
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Hakemli Kongre / Sempozyum Bildiri Kitaplarında Yer Alan Yayınlar

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II. **Optical properties of GaN and InN on quartz grown by hollow-cathode plasma-assisted atomic layer deposition**
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III. **Critical Thickness on Optical Properties at UV VIS and Infrared Region of GaN Thin Films Grown by Hollow Cathode Assisted Atomic Layer Deposition**
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IV. **THE ROLE OF THICKNESS ON INFRARED OPTICAL PROPERTIES OF GALLIUM NITRIDE THIN FILMS GROWN BY HOLLOW CATHODE PLASMA ASSITED ATOMIC LAYER DEPOSITION**
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Turkisk Physical Society 32nd International Physics Congress, Bodrum, Türkiye, 6 - 09 Eylül 2016

V. **Infrared dielectric functions phonon modes and band gap properties of plasma assisted ALD grown InxGa1 xN films**
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VII. **Influence of N2 H2 and N2 Plasma on Binary III Nitride Films Prepared by Hollow Cathode Plasma Assisted Atomic Layer Deposition**
ALEVLİ M., Gungor N., Ozgit Akgun C., Haider A., Kızır S., BIYIKLI N.
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IX. **Hollow Cathode Plasma Assisted Atomic Layer Deposition of Wurtzite InN and InxGa1 xN Thin Films with Low Impurity Content**
Haider A., Kizir S., Ozgit Akgun C., Goldenberg E., ALEVLİ M., OKYAY A. K., BIYIKLI N.
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Desteklenen Projeler

Alevli M., TÜBİTAK Projesi, Atomik Katman Büyütme Yöntemi Ile Kaplanan GaN Galyum Nitrat Ince Filmlerinin Optik Karakterizasyonu, 2014 - 2015

Metrikler

Yayın: 54
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